

Electronic Acknowledgement Receipt

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Application Number:	10801234
International Application Number:	
Confirmation Number:	2028
Title of Invention:	AN IMPROVED HIGH-VOLTAGE MOS TRANSISTOR
First Named Inventor/Applicant Name:	Fu-Hsin Chen
Customer Number:	42717
Filer:	David M. Odell/Bonnie Boyle
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File Listing:

Document Number	Document Description	File Name	File Size(Bytes)	Multi Part /.zip	Pages (if appl.)
1	Supplemental Response or Supplemental Amendment	79SupplementalResponseto NFOA.pdf	649891	no	11

Warnings:

Information:	
Total Files Size (in bytes):	649891
<p>This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.</p> <p><u>New Applications Under 35 U.S.C. 111</u> If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.</p> <p><u>National Stage of an International Application under 35 U.S.C. 371</u> If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.</p>	